11/4/3

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(Use several sheets if necessary)	Kazuhiro TSURUTA		
Sheet 1 of <u>1</u>	FILING DATE 11/4/03	GROUP .	

Ref.	E	U.S.PATENT DOCUMENTS			()5			
Ret.	Examiner's Document				Class/		(If appropriate)	
Desig, Initials		Number	Date	Name	Subclass		Filing Date	
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		"FABRICATION OF THICK SILICON DIOXIDE LAYERS USING DRIE, OXIDATION AND TRENCH REFILL" by Zhang et al.; Technical Digest of The Fifteenth IEEE International Conference on Micro Electro Mechanical Systems; 2002; pp., 160–163 (Dicussed in 1935 3-4 in the spect)
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